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MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFC39V5964A

5.9 ~ 6.4GHz BAND 8W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC39V5964A is an internally impedance-matched GaAs power FET especially designed for use in 5.9 ~ 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 8W (TYP.) @ f=5.9~6.4GHz High power gain GLP = 10.5 dB (TYP.) @ f=5.9~6.4GHz High power added efficiency P.A.E. = 30 % (TYP.) @ f=5.9~6.4GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @Po=28dBm S.C.L.

APPLICATION

item 01 : 5.9~6.4 GHz band power amplifier item 51: 5.9~6.4 GHz band digital radio communication

QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

VDS = 10 (V)ID = 2.4 (A)RG= 50 (ohm)

Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS		(Ta=25 deg.C)		
Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	-15	V	
VGSO	Gate to source voltage	-15	V	
ID	Drain current	7.5	Α	
IGR	Reverse gate current	-20	mA	
IGF	Forward gate current	42	mA	
PT	Total power dissipation *1	42.8	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	
*4 . To OF				

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or mishap.

*1 : Tc=25 deg.C

F

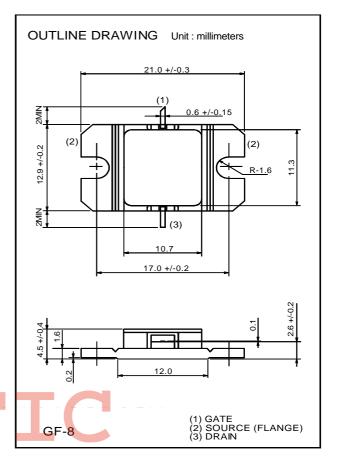
ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)						
Parameter	Test conditions	Limits			Unit	
Falametei		Min.	Тур.	Max.	Offic	
Saturated drain current	VDS=3V, VGS=0V	-	-	7.5	А	
Transconductance	VDS=3V, ID=2.2A	-	2	-	S	
Gate to source cut-off voltage	VDS=3V, ID=20mA	-	-	-4.5	V	
Output power at 1dB gain compression		38	39.5	-	dBm	
Linear power gain	VDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz	8	10.5	-	dB	
Drain current		-	-	3	А	
Power added efficiency		-	30	-	%	
3rd order IM distortion *1		-42	-45	-	dBc	
Thermal resistance *2	Delta Vf method	-	-	3.5	deg.C/W	
	Parameter Saturated drain current Transconductance Gate to source cut-off voltage Output power at 1dB gain compression Linear power gain Drain current Power added efficiency 3rd order IM distortion *1	ParameterTest conditionsSaturated drain currentVDS=3V, VGS=0VTransconductanceVDS=3V, ID=2.2AGate to source cut-off voltageVDS=3V, ID=20mAOutput power at 1dB gain compressionVDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHzDrain currentPower added efficiency3rd order IM distortion *1*1	Parameter Test conditions Min. Saturated drain current VDS=3V, VGS=0V - Transconductance VDS=3V, ID=2.2A - Gate to source cut-off voltage VDS=3V, ID=20mA - Output power at 1dB gain compression vDS=10V, ID(RF off)=2.4A, f=5.9-6.4GHz 38 Linear power gain vDS=10V, ID(RF off)=2.4A, f=5.9-6.4GHz - Power added efficiency - - 3rd order IM distortion *1 -42	Parameter Test conditions Limits Saturated drain current VDS=3V, VGS=0V - - Transconductance VDS=3V, ID=2.2A - 2 Gate to source cut-off voltage VDS=3V, ID=20mA - - Output power at 1dB gain compression VDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz 38 39.5 Linear power gain VDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz 8 10.5 Drain current - - - Power added efficiency *1 - -	ParameterTest conditionsImitsMin.Typ.Max.Saturated drain currentVDS=3V, VGS=0V7.5TransconductanceVDS=3V, ID=2.2A-2-Gate to source cut-off voltageVDS=3V, ID=20mA4.5Output power at 1dB gain compressionVDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz810.5-Linear power gainVDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz810.5-Power added efficiency-30-3rd order IM distortion *1-42-45-	

*1 : item -51, 2 tone test, Po=28dBm Single Carrier Level, f=6.4GHz, Delta f=10MHz

*2 : Channel to case



June/2004 http://www.kttic.com



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